

**TOSHIBA****TFR4N, TFR4T**

TOSHIBA FAST RECOVERY DIODE SILICON DIFFUSED TYPE

**TFR4N, TFR4T**

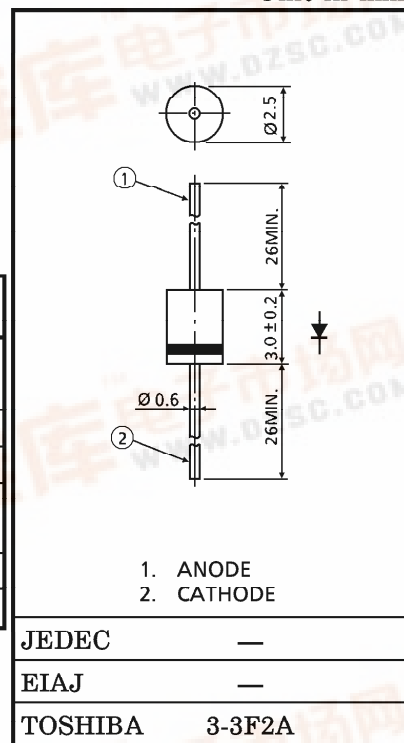
STROBO FLASHER APPLICATIONS. (FAST RECOVERY)

Unit in mm

- Average Forward Current :  $I_F (AV) = 0.3A$
- Repetitive Peak Reverse Voltage :  $V_{RRM} = 1000, 1500V$
- Reverse Recovery Time :  $t_{rr} = 4\mu s$

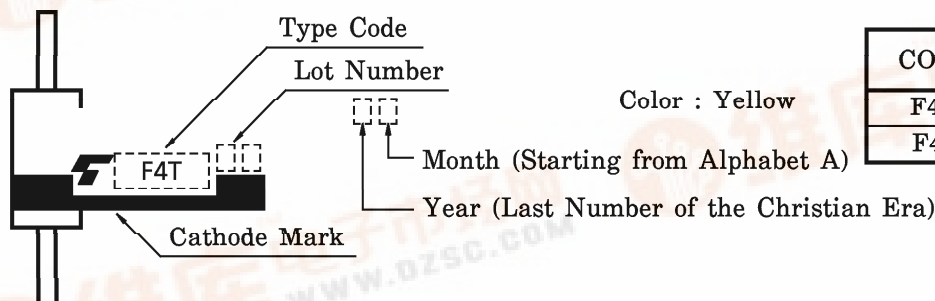
**MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	TFR4N	1000	V
	TFR4T	1500	
Average Forward Current	$I_F (AV)$	0.3	A
$I^2t$ Limit Value ( $t=1\sim 10ms$ )	$I^2t$	0.5	$A^2s$
Peak One Cycle Surge Forward Current (Non Repetitive)	$I_{FSM}$	10 (50Hz)	A
Junction Temperature	$T_j$	$-40\sim 125$	$^{\circ}C$
Storage Temperature Range	$T_{stg}$	$-40\sim 125$	$^{\circ}C$

**ELECTRICAL CHARACTERISTICS** ( $T_a = 25^{\circ}C$ )

Weight : 0.18g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	$V_{FM}$	$I_{FM} = 0.5A$	—	—	1.5	V
Repetitive Peak Reverse Current	$I_{RRM}$	$V_{RRM} = \text{Rated}$	—	—	10	$\mu A$
Reverse Recovery Time	$t_{rr}$	$I_F = 20mA, I_R = 1mA$	—	—	4	$\mu s$

**MARKING**

CODE	TYPE
F4N	TFR4N
F4T	TFR4T

961001FAA2

TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

